DUSEU

2-Input NAND **Schmitt-Trigger with Open Drain Output**

NLV74VHC1G135

The NLV74VHC1G135 is a single gate CMOS Schmitt NAND trigger with an open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3-state output which provides high noise immunity and stable output.

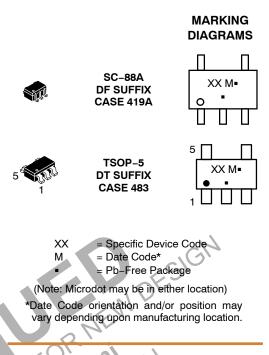
The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when $V_{CC} = 0$ V and when the output voltage exceeds V_{CC}. These input and output structures help prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 4.9 ns tpp at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5
- IOFF Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A and TSOP-5 Packages
- Chip Complexity < 100 FETs
- ONTAC • NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Figure 1. Logic Symbol



ORDERING INFORMATION

JEFOR INFORM See detailed ordering, marking and shipping information on page 7 of this data sheet.

CONNN

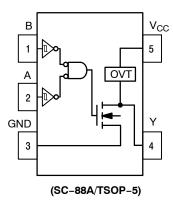


Figure 2. Pinout (Top View)

FUNCTION TABLE

PIN ASSIGNMENT (SC-88A/TSOP-5)

Pin	Function				
1	В				
2	A				
3	GND				
4	Y				
5	V _{CC}				

Output Input Α В γ z L L THIS DEVICE PLEASENTATIVE FOR INFORMATION PLEASENT FOR INFORM

MAXIMUM RATINGS

Symbol	С	Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V	
V _{OUT}	DC Output Voltage	DC Output Voltage 1Gxx		V
		1GTxx Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +7.0 \\ -0.5 \text{ to } +7.0 \end{array}$	
Ι _{ΙΚ}	DC Input Diode Current	V _{IN} < GND	-20	mA
I _{OK}	DC Output Diode Current	1Gxx $V_{OUT} > V_{CC}, V_{OUT} < GND$	±20	mA
		1GTxx V _{OUT} < GND	-20	
I _{OUT}	DC Output Source/Sink Current		±25	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pir	n or Ground Pin	±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	∕ °C
ΤL	Lead Temperature, 1 mm from Ca	se for 10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC-88A TSOP-5	377 320	°C/W
PD	Power Dissipation in Still Air	SC-88A TSOP-5	332 390	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)	Olm Z I IM	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- should not be assumed, damage may occur and reliability may be affected.
 Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
 Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	CI	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage			5.5	V
V _{IN}	DC Input Voltage	0	5.5	V	
V _{OUT}	DC Output Voltage	1Gxx	0	V _{CC}	V
		1GTxx Active-Mode (High or Low State) Tri-State Mode Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS					IGN						
			v _{cc}	Т	A = 25°	С	-40°C ≤ .	T _A ≤ 85°C	55°C ≤ T	_ ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Мах	Min	Max	Unit
V_{T+}	Positive Input Threshold Voltage		3.0 4.5 5.5	1.2 1.75 2.15	2.0 3.0 3.6	2.2 3.15 3.85	-	2.2 3.15 3.85		2.2 3.15 3.85	V
V _{T-}	Negative Input Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9	1.9 2.75 3.35	0.9 1.35 1.65	s <u>e</u> m	0.9 1.35 1.65	- -	V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu \text{A}$	2.0 3.0 4.5	<u>, T</u>	0.0 0.0 0.0	0.1 0.1 0.1	<u> </u>	0.1 0.1 0.1	- - -	0.1 0.1 0.1	V
	G	I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5	<u> 7</u>	JE.	0.36 0.36	-	0.44 0.44	-	0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	b,	_	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	_	_	1.0	-	20	-	40	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V	0.0	-	-	1.0	-	10	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

				Т	A = 25°	C	-40°C ≤ 1	Γ _A ≤ 85°C	–55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PZL} Propagation Delay,	C _L = 15 pF	3.0 to 3.6	-	7.6	11.9	-	14.0	-	16.1	ns	
	(A or B) to Y (Figures 3 and 4)	C _L = 50 pF		-	10.1	15.4	-	17.5	-	19.6	
		C _L = 15 pF	4.5 to 5.5	-	4.9	7.7	-	9.0	-	10.3	
		C _L = 50 pF		-	6.4	9.7	-	11.0	-	12.3	
t _{PLZ}	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	-	7.6	11.9	-	14.0	-	16.1	ns
	(A or B) to Y (Figures 3 and 4)	C _L = 50 pF		-	10.1	15.4	-	17.5	-	19.6	1
		C _L = 15 pF	4.5 to 5.5	-	4.9	7.7	-	9.0	-	10.3	1
		C _L = 50 pF		-	6.4	9.7	-	11.0	-	12.3	1
C _{IN}	Maximum Input Capacitance			-	5.0	10	-	10	-	10	pF
		•	-				•			CN'	•

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 5)	16.0	pF
5. C _{PD} is Averaç	defined as the value of the internal equivalent capacitance which is calculated from the ge operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \bullet V_{CC}$ consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.	operating current consumption witho	out load.
,	THIS DEVICE PLEASENTS REPRESENT		

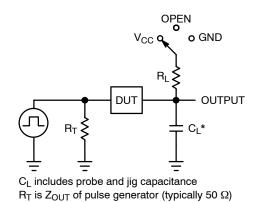
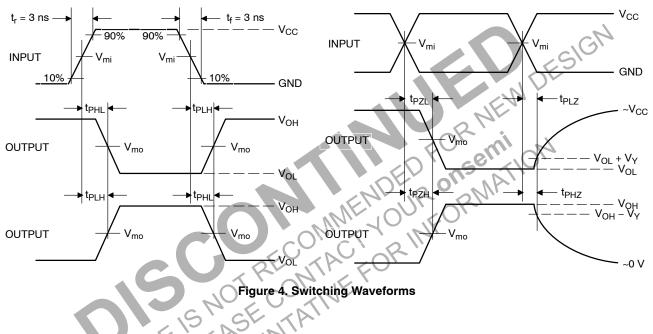


Figure 3. Test Circuit

f = 1 MHz

Test	Switch Position	C _L , pF	R_L, Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	Х
t _{PLZ} / t _{PZL}	V _{CC}		1 k
t _{PHZ} / t _{PZH}	GND		1 k

X = Don't Care



	NCENERGE	Vmo		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

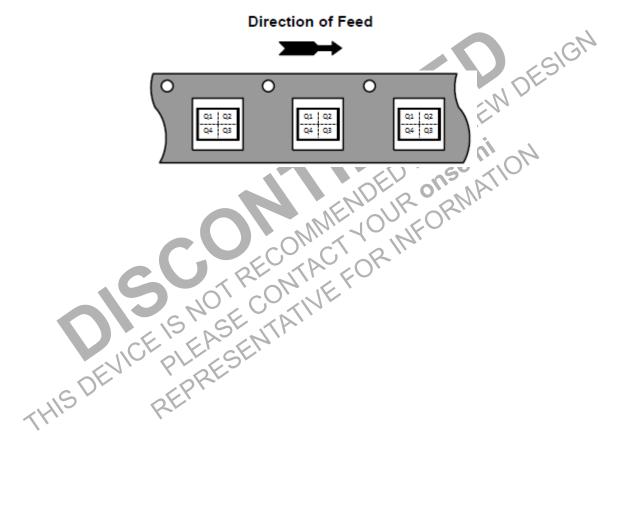
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
M74VHC1G135DFT1G-L22038	SC-88A	VZ	Q2	3000 / Tape & Reel
M74VHC1G135DFT2G-L22038	SC-88A	VZ	Q4	3000 / Tape & Reel
NLVVHC1G135DFT2G*	SC-88A	VZ	Q4	3000 / Tape & Reel
M74VHC1G135DTT1G	TSOP-5	VZ	Q4	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL



onsemi

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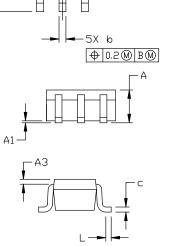
DATE 11 APR 2023



SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

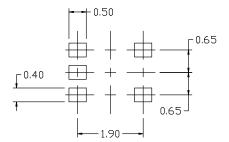
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



e

F1



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS				
MIM	MIN.	NDM,	MAX.		
А	0.80	0.95	1.10		
A1			0.10		
AЗ		0.20 REF	-		
b	0.10	0.20	0.30		
С	0.10		0.25		
D	1.80	2.00	2.20		
E	2.00	2.10	2,20		
E1	1.15	1.25	1.35		
e		0.65 BS	С		
L	0.10	0.15	0.30		

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

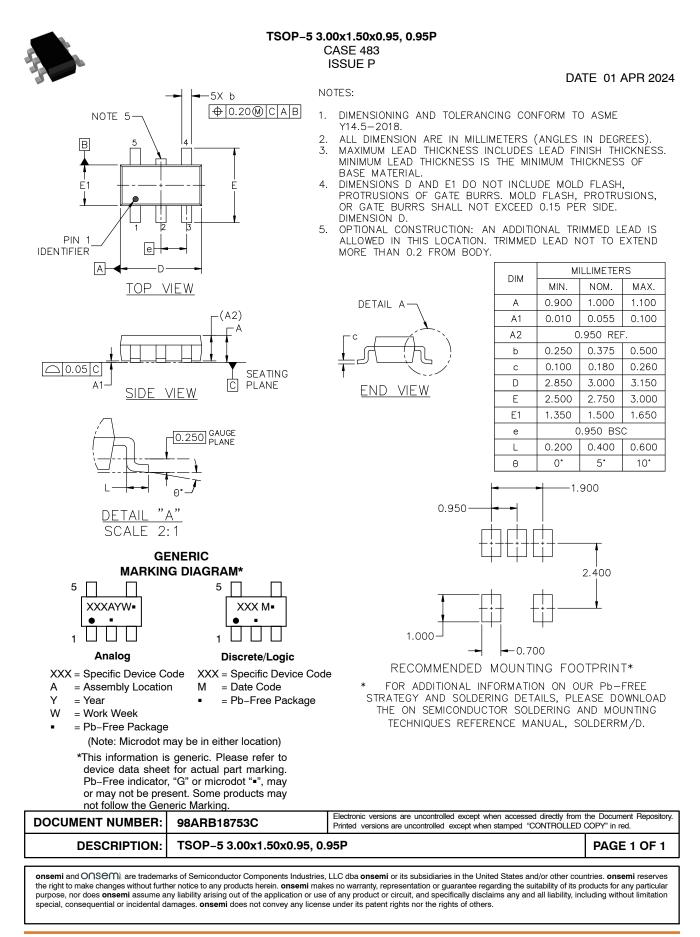
M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

DESCRIPTION:	SC-88A (SC-70-		ns are uncontrolled except w	vhen stamped "CONTROLLED (COPY" in red. PAGE 1 OF 1
DOCUMENT NUMBER:	98ASB42984B			t when accessed directly from	
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called efer to the device
STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E

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